Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1633	@ad<="20030930" and (257/79-80).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
L2	1826	@ad<="20030930" and (385/130-131).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
L3	862	@ad<="20030930" and (257/96-97).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
L4	1867	@ad<="20030930" and (257/98).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
L5	1005	@ad<="20030930" and (257/88-89).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
L6	194	@ad<="20030930" and (257/93).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
L7	1252	@ad<="20030930" and (257/94-95).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
L8	876	@ad<="20030930" and (372/108).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
L9	1364	@ad<="20030930" and (372/96).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
L10	2267	@ad<="20030930" and (372/46).ccls. or (372/45).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S1	14	@ad<="20030930" and 'light emitting device' and 'mesoporous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 08:26

S2	0	@ad<="20030930" and 'light emitting device' and 'periodic porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 13:47
S3	498	@ad<="20030930" and 'light emitting device' and 'rohm'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 13:51
S4	39	@ad<="20030930" and 'light emitting device' and 'rohm' and 'inorganic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 13:55
S5	1	@ad<="20030930" and 'light emitting device' and 'rohm' and 'inorganic insulating'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 13:52
S6	12	@ad<="20030930" and 'light emitting diode' same 'inorganic' same 'protective'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:28
S7	30	@ad<="20030930" and 'light emitting device' same 'inorganic' same 'protective'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:01
S8	32	@ad<="20030930" and 'light emitting device' and 'clad layer' and 'active layer' and 'inorganic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:02
S10	171	@ad<="20030930" and 'light emitting device' and 'clad layer' and 'active layer' and 'mesa'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 08:37
S11	4	@ad<="20030930" and 'light emitting device' and 'clad layer' and 'active layer' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:11
S12	4	@ad<="20030930" and 'laser' and 'clad layer' and 'active layer' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:11
S13	11	@ad<="20030930" and 'laser' and 'clad' and 'active' and 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:28

S14	54	@ad<="20030930" and 'laser' and 'clad' and 'active' and 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:18
S15	33	@ad<="20030930" and 'semiconductor laser' and 'inorganic protective'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:25
S16	82	@ad<="20030930" and 'semiconductor laser' and 'inorganic' with 'porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:35
S17	773	@ad<="20030930" and 'LED' and 'inorganic' with 'porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 16:11
S18	2	@ad<="20030930" and 'led' and 'clad' and 'active' and 'inorganic' with 'porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:42
S19	67	@ad<="20030930" and 'inorganic' with 'mesoporous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:04
S20	0	@ad<="20030930" and 'semiconductor laser' with 'mesoporous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:39
S21	0	@ad<="20030930" and 'semiconductor laser' same 'mesoporous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:39
S22	4	@ad<="20030930" and 'semiconductor laser' and 'mesoporous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:34
S23	1	"20020018610".PN.	US-PGPUB	OR	ON	2005/02/14 14:40
S24	1	"6538801".PN.	USPAT; USOCR	OR	ON	2005/02/14 14:40
S25	56	@ad<="20030930" and 'inorganic' with 'vacancy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:50

S26	14	@ad<="20030930" and 'inorganic' same 'dielectric' same 'vacancy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 14:50
S27	5	@ad<="20030930" and 'mesa' and 'n-type clad' and 'active' and 'p-type clad' and 'inorganic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:51
S28	1554	@ad<="20030930" and (257/79-80).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
S29	1772	@ad<="20030930" and (385/130-131).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
S30	1	"20030146440".PN.	US-PGPUB	OR	ON	2005/02/15 08:39
S31	1	"20030146440".PN.	US-PGPUB	OR	ON	2005/02/15 08:39
S32	1	"6546034".PN.	USPAT; USOCR	OR	ON	2005/02/15 08:40
S33	1	"6141363".PN.	USPAT; USOCR	OR	ON	2005/02/15 08:42
S34	835	@ad<="20030930" and (257/96-97).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
S35	1791	@ad<="20030930" and (257/98). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:35
S36	320	@ad<="20030930" and (257/86-87).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 08:44
S37	956	@ad<="20030930" and (257/88-89).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S38	189	@ad<="20030930" and (257/93). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S39	1222	@ad<="20030930" and (257/94-95).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36

S40	10	@ad<="20030930" and 'mesa' and 'n-type' with 'p-type' with 'cladding' and 'active' and 'inorganic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 08:46
S41	1338	@ad<="20030930" and (372/96).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S42	869	@ad<="20030930" and (372/108).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S43	5757	@ad<="20030930" and (372/46).ccls. or (372/45).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 06:36
S45	47	oku.in. and 'rohm'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:13
S46	1	"5998819".PN.	USPAT; USOCR	OR	ON	2005/02/15 09:33
S47	2	'ep 1094506'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:42
S48	2	'ep 1124252'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:46
S49	2	("5021260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/15 09:44
S50	2	'jp 2001118841'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:48
S51	2	'jp 2002217190'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:49

S52	21	'0175957'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:51
S53	2	'JP 2001351911'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 09:57
S54	4	("5405805").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/15 09:53
S55	26	@ad<="20030930" and 'mesoporous silica' same '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:08
S56	6	@ad<="20030930" and 'mesoporous silica' with '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:05
S57	11	@ad<="20030930" and 'dielectric' and 'porous silica' same '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:12
S58	32	@ad<="20030930" and 'dielectric' and 'mesoporous' same '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 11:27
S59	24	@ad<="20030930" and 'dielectric' same 'mesoporous' same '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:19
S60	38	@ad<="20030930" and 'mesa' and 'n-type clad' and 'active' and 'p-type clad' and 'insulating'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:52
S61	23	@ad<="20030930" and 'mesa' and 'n-type clad' and 'active' and 'p-type clad' and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:56
S62	19	@ad<="20020930" and 'mesa' and 'n-type clad' and 'active' and 'p-type clad' and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 10:56

S63	3	("6693286").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/15 11:26
S64	32	@ad<="20030930" and 'dielectric' same 'porous' same 'parallel' same 'adjacent'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 11:57
S65	4	("5621260").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/15 11:57
S66	4	@ad<="20030930" and 'semiconductor laser' same 'porous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:35
S67	85	@ad<="20030930" and 'laser' same 'porous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:36
S68	0	@ad<="20030930" and 'optical laser' same 'porous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:36
S69	0	@ad<="20030930" and 'light emission' same 'porous silica'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:36
S70	22	@ad<="20030930" and 'light emission' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:45
S71	9	@ad<="20030930" and 'semiconductor laser' same 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 12:43
S72	1	@ad<="20030930" and 'semiconductor laser' same 'low k'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:32
S74	69	ponnekanti.in. and 'applied'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:13

S75	60	ponnekanti.in. and 'applied materials'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:14
S76	8	ponnekanti.in. and 'low dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:14
S77	9	@ad<="20030930" and 'CTAB' same 'TMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:35
S78	42	@ad<="20030930" and 'CTAB' and 'TEOS' and '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:37
S79	0	@ad<="20030930" and 'CTAB' same 'TEOS' same '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:36
S80	5	@ad<="20030930" and 'CTAB' and 'TEOS' and 'porous' with '50%'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 14:37
S81	7	@ad<="20030930" and 'dielectric' same 'periodic porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 16:13
S82	3	@ad<="20030930" and 'low dielectric' same 'periodic porous'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/15 16:13